L Number	Hits	Search Text	DB	Time stamp
-	149	(nitride near semiconductor) and (buffer near layer) and (active near	USPAT;	2002/09/19 14:41
		layer) and (clad\$5 near layer) and indium	US-PGPUB;	
			EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	
-	131	(nitride near semiconductor) and (buffer near layer) and (active near	USPAT;	2002/09/19 14:50
		layer) and (clad\$5 near layer) and indium and substrate and electrode	US-PGPUB;	
			ЕРО; ЈРО;	
i			DERWENT;	
			IBM_TDB	
-	20	(nitride near semiconductor) and ((buffer near layer) with indium)	USPAT;	2002/09/19 17:22
		and (active near layer) and (clad\$5 near layer) and substrate and	US-PGPUB;	
		electrode	EPO; JPO;	
			DERWENT;	٠
		·	IBM_TDB	·
-	28	(nitride near semiconductor) and (buffer near layer) and (active near	USPAT;	2002/09/19 14:52
		layer) and (clad\$5 near layer) and indium and substrate and electrode	US-PGPUB;	
		and absorb\$6	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	21	((nitride near semiconductor) and (buffer near layer) and (active near	USPAT;	2002/09/19 14:52
		layer) and (clad\$5 near layer) and indium and substrate and electrode	US-PGPUB;	
		and absorb\$6) not ((nitride near semiconductor) and ((buffer near	ЕРО; ЈРО;	
		layer) with indium) and (active near layer) and (clad\$5 near layer)	DERWENT;	
		and substrate and electrode)	IBM_TDB	
-	6	(laser near chip) and (photoelectric or (photo adj electric)) and	USPAT;	2002/09/19 17:42
		block\$6 and buffer and substrate	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		//	IBM_TDB	0000/00/10 15 44
-	160	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB;	2002/09/19 17:44
		and blockso and buffer and substrate	EPO; JPO;	
			DERWENT;	
į			IBM_TDB	
_	14	(laser near semiconductor) and (photoelectric or (photo adj electric))	USPAT;	2002/09/19 17:46
	•••	and block\$6 and buffer and substrate and (laser near3 chip)	US-PGPUB;	2002/ 03/ 13 11:10
	ĺ		EPO; JPO;	
	!		DERWENT;	
	,		IBM_TDB	
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric)	USPAT;	2002/09/20 07:00
	!	or (photodetector) (photodiode) or (photo adj detector) or (photo ajd	US-PGPUB;	
		diode)) and block\$6 and buffer and substrate and (laser near3 chip)	ЕРО; ЈРО;	
		"	DERWENT;	
İ			IBM_TDB	
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo	USPAT;	2002/09/20 07:03
		adj electric) or (photodetector) (photodiode) or (photo adj detector)	US-PGPUB;	
	}	or (photo ajd diode)) and block\$6 and buffer and substrate	EPO; JPO;	
		_	DERWENT;	
			IBM_TDB	
-	40	(semiconductor near laser near3 chip) and (photoelectric or (photo	USPAT;	2002/09/20 10:59
		adj electric) or (photodetector) or (photodiode) or (photo adj	US-PGPUB;	
		detector) or (photo adj diode)) and block\$6 and buffer and substrate	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	23	((semiconductor near laser near3 chip) and (photoelectric or (photo	USPAT;	2002/09/20 07:29
		adj electric) or (photodetector) or (photodiode) or (photo adj	US-PGPUB;	•
		detector) or (photo adj diode)) and block\$6 and buffer and substrate)	EPO; JPO;	
		and 372/\$	DERWENT;	
			IBM_TDB	

Γ-	5	(semiconductor near laser near3 chip) and ((photoelectric or (photo	USPAT;	2002/09/20 10:58
	i	adj electric) or (photodetector) or (photodiode) or (photo adj	US-PGPUB;	
		detector) or (photo adj diode)) same block\$6) and buffer and	EPO; JPO;	
		substrate	DERWENT;	
		,	IBM_TDB	
_	0	(semiconductor near laser near3 chip) and ((photoelectric or (photo	USPAT;	2002/09/20 11:01
1		adj electric) or (photodetector) or (photodiode) or (photo adj	US-PGPUB;	
		detector) or (photo adj diode)) same (block\$6 near layer)) and buffer	EPO; JPO;	
		and substrate	DERWENT;	
			IBM_TDB	
_	26	(semiconductor near laser near3 chip) and (photoelectric or (photo	USPAT;	2002/09/20 11:02
		adj electric) or (photodetector) or (photodiode) or (photo adj	US-PGPUB;	
		detector) or (photo adj diode)) and (block\$6 near layer) and buffer	EPO; JPO;	
		and substrate	DERWENT;	
			IBM_TDB	